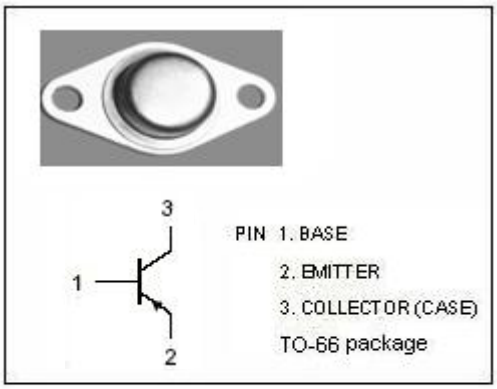
isc Silicon PNP Power Transistors 3CD3C

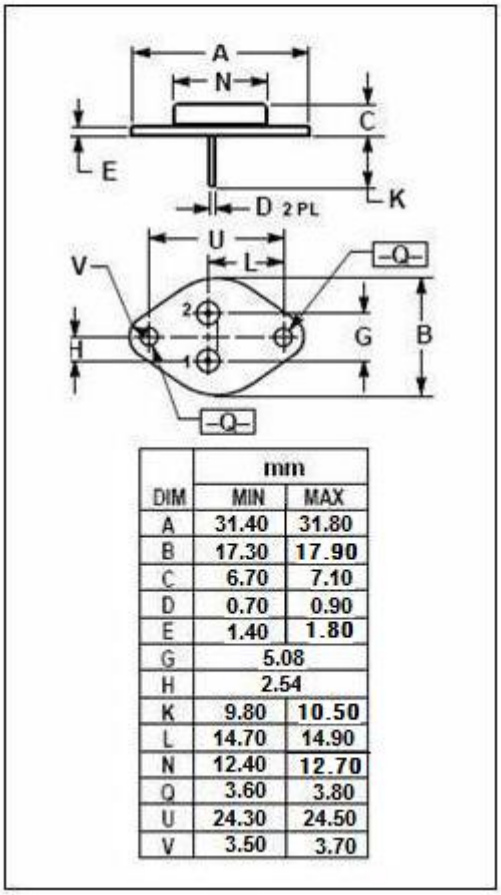


DESCRIPTION

- Large collector current
- Low collector saturation voltage
- High power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in DC-DC converter
- Driver of solenoid or motor



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-1	A
P_C	Collector Power Dissipation@Tc=75℃	10	W
T_J	Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	12.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C=- 3mA ; I_B= 0	-80		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E=- 3mA ; I_C= 0	-4		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C=- 0.5A; I_B= -0.1A		-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -0.1A		-1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}=- 80V; I_B= 0		-1.0	mA
I_{CBO}	Collector Cutoff Current	V_{CB}=- 80V; I_E= 0		-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0		-1.0	mA
h_{FE}	DC Current Gain	I_C= -0.5A; V_{CE}=-10V	10	180	